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Asami

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(54) **PHOTOELECTRIC CONVERSION DEVICE**

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H01L 31/076 (2012.01)

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CPC **H01L 31/028** (2013.01); **H01L 27/302** (2013.01); **H01L 31/03682** (2013.01); **H01L 31/03685** (2013.01); **H01L 31/03762** (2013.01); **H01L 31/0687** (2013.01); **H01L 31/0725** (2013.01); **H01L 31/076** (2013.01); **Y02E 10/544** (2013.01); **Y02E 10/545** (2013.01); **Y02E 10/546** (2013.01); **Y02E 10/548** (2013.01); **Y02E 10/547** (2013.01)

(58) **Field of Classification Search**

None

See application file for complete search history.

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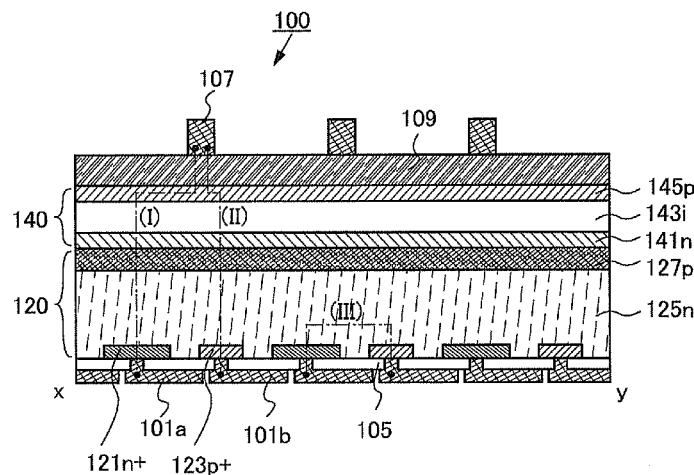
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(57) **ABSTRACT**

A photoelectric conversion device includes a first cell including a photoelectric conversion layer, a second cell over the first cell including a photoelectric conversion layer formed of a material having a wider band gap than that of the first cell, first and second electrodes under a surface of the first cell which is opposite to the second cell, and a third electrode over a surface of the second cell which is opposite to the first cell. The first and second cells each include a p-n or p-i-n junction, the first and second cells are in contact with each other and a p-n junction is formed in a contact portion therebetween, the first cell is electrically connected to the first and second electrodes to form a back contact structure, and the second cell is electrically connected to the third electrode.

8 Claims, 12 Drawing Sheets



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FIG. 1

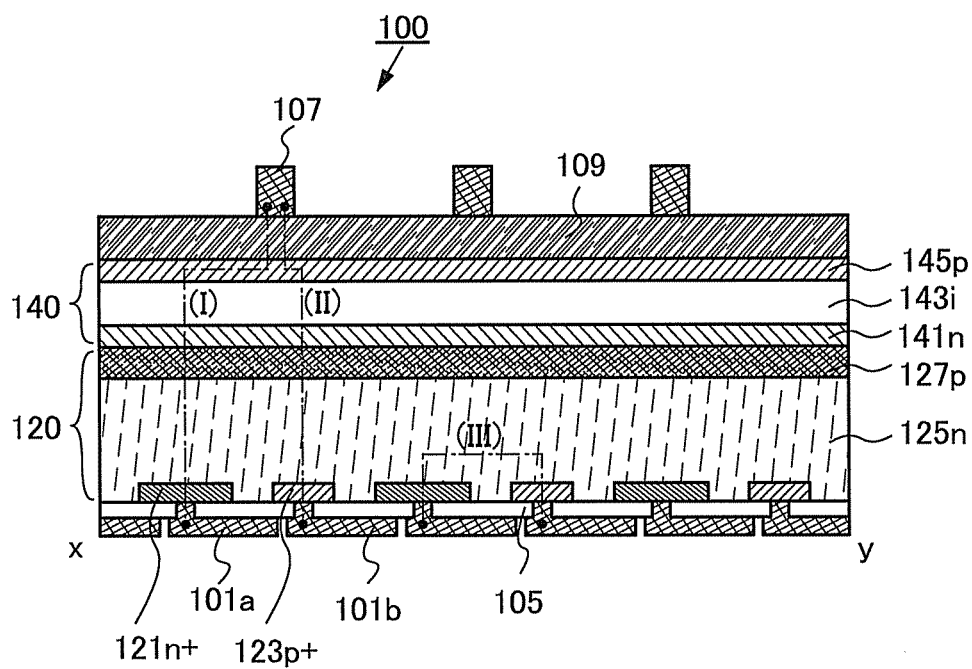


FIG. 2A

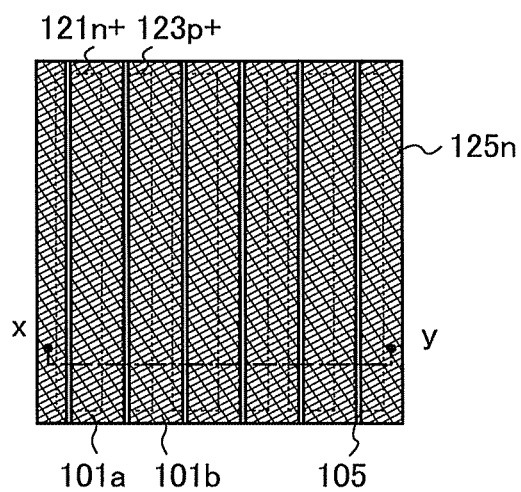


FIG. 2B

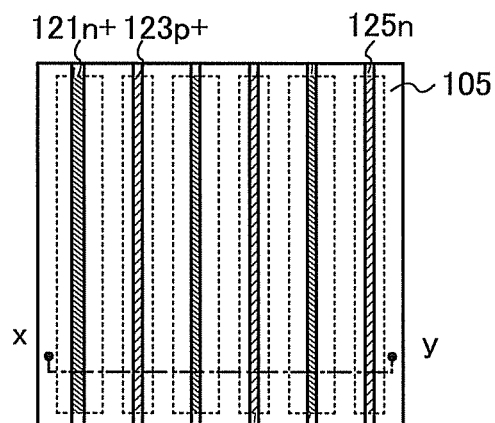
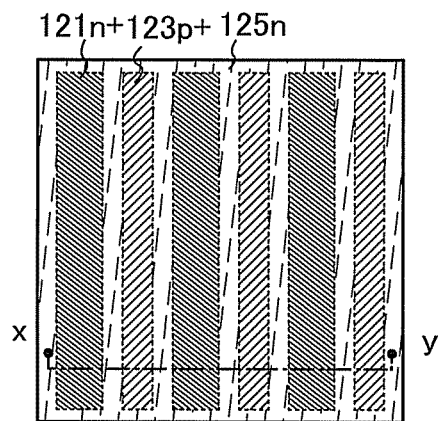


FIG. 2C



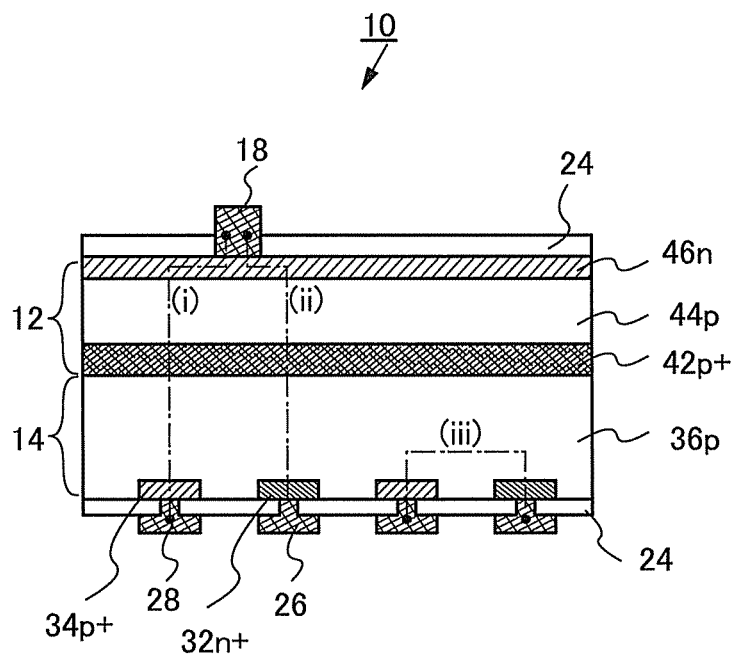


FIG. 4

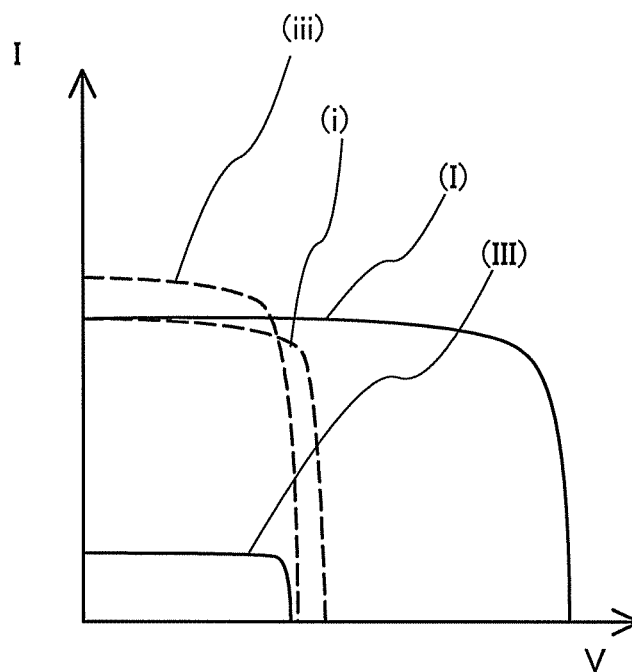


FIG. 5A

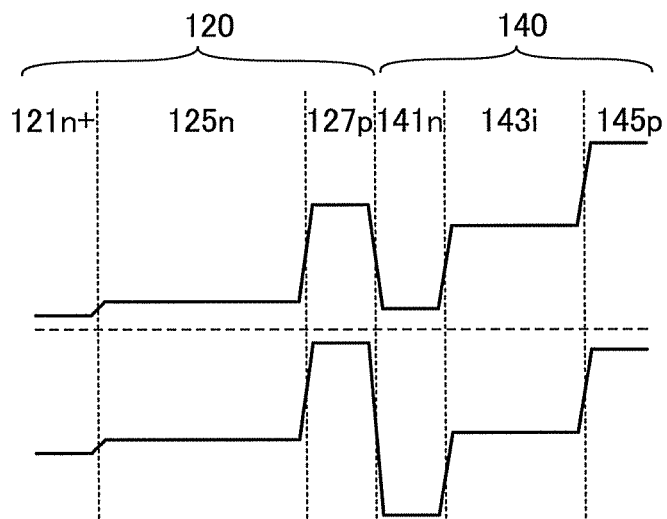


FIG. 5B

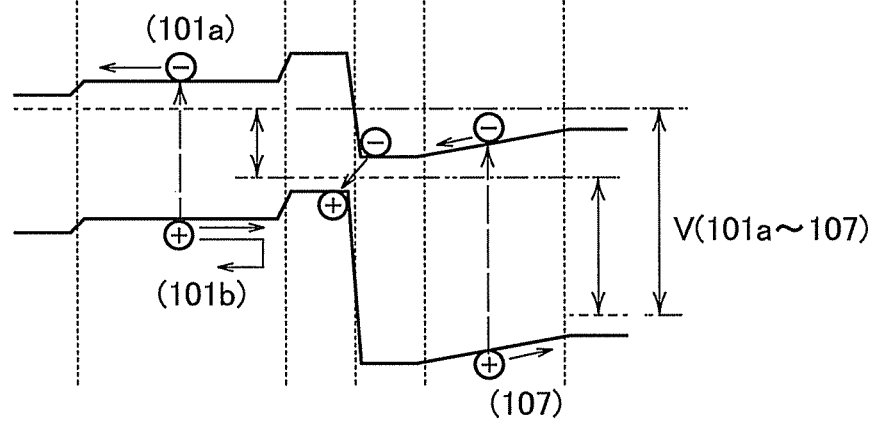


FIG. 6A

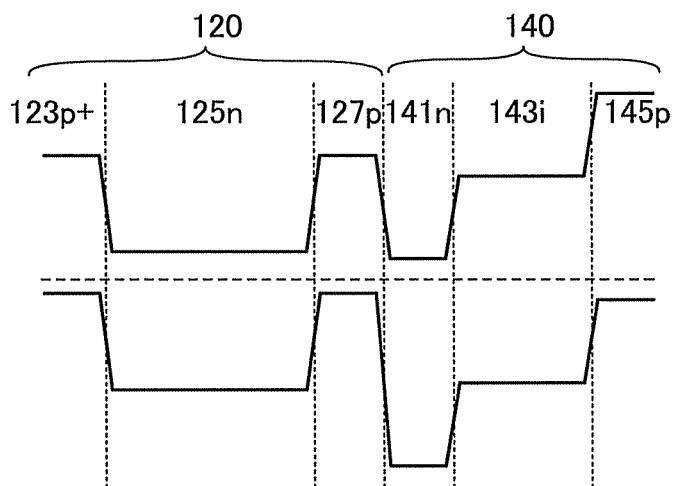


FIG. 6B

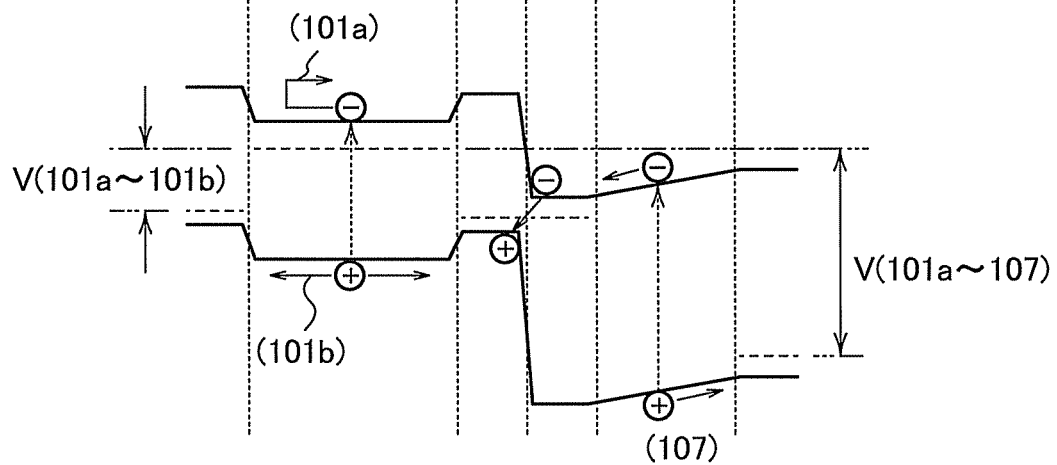


FIG. 7A

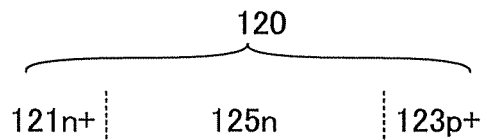


FIG. 7B

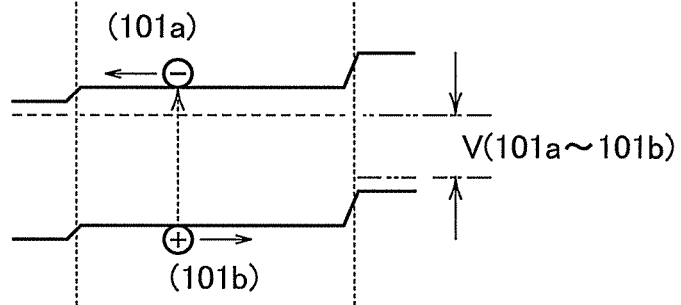


FIG. 8A

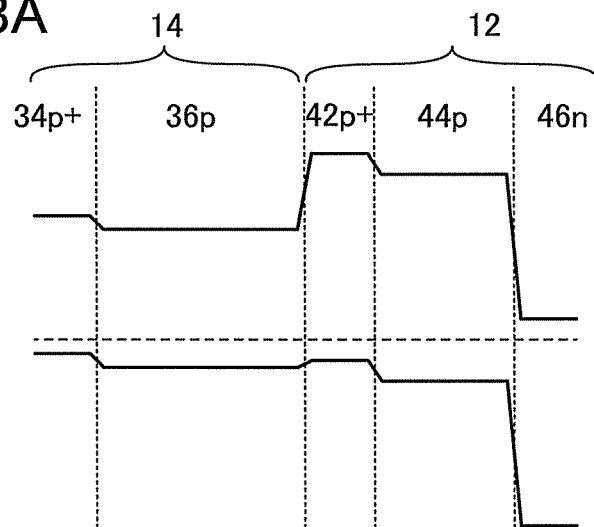


FIG. 8B

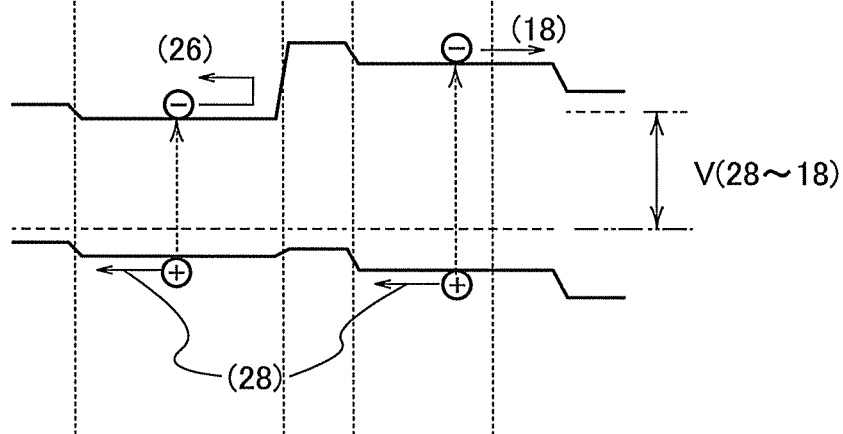


FIG. 9A

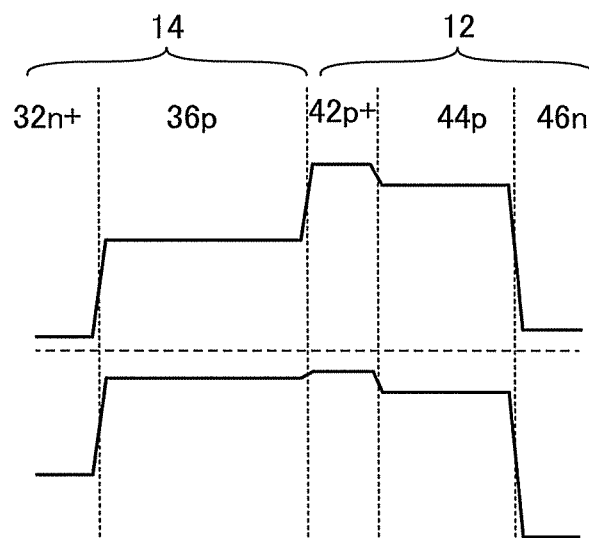


FIG. 9B

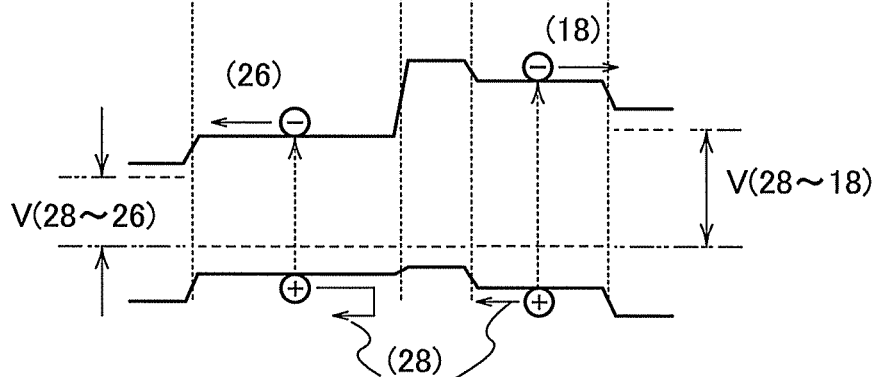


FIG. 10A

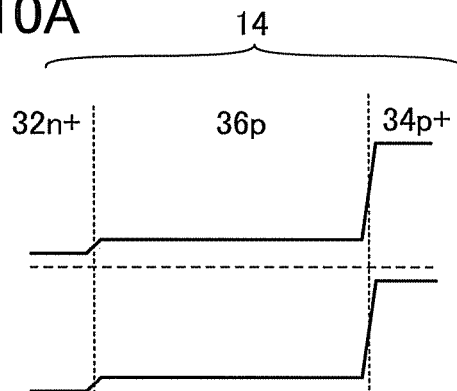


FIG. 10B

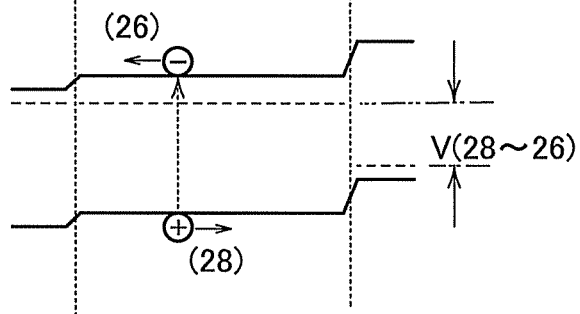


FIG. 11

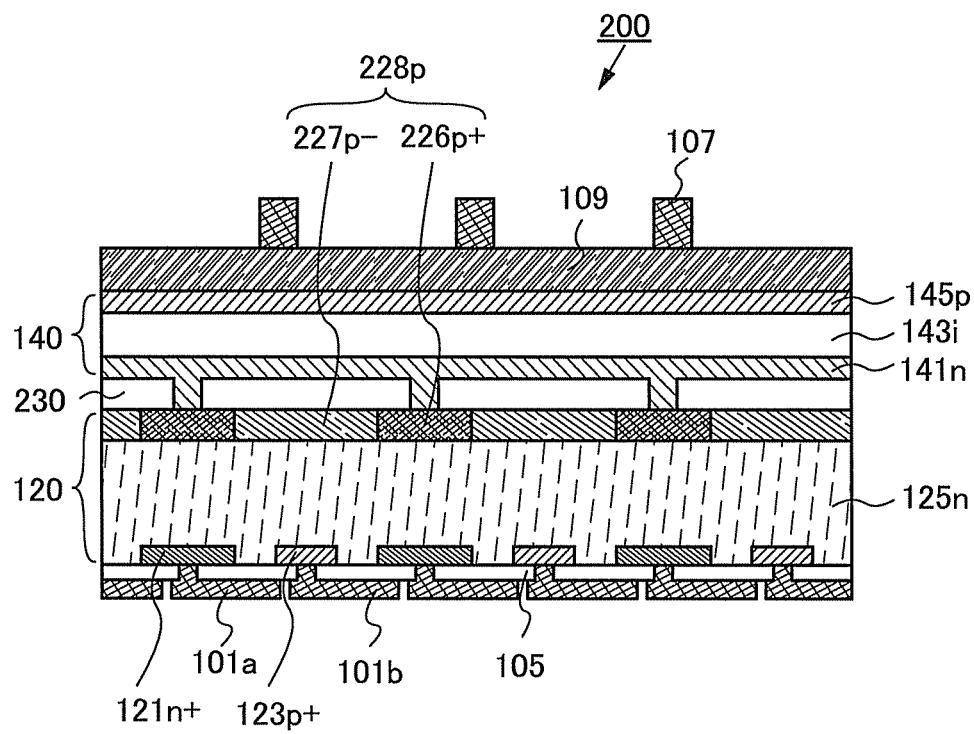


FIG. 12A

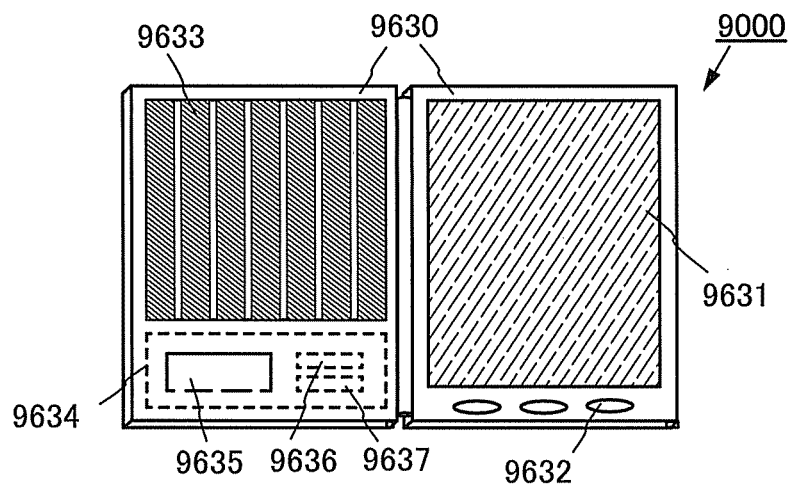
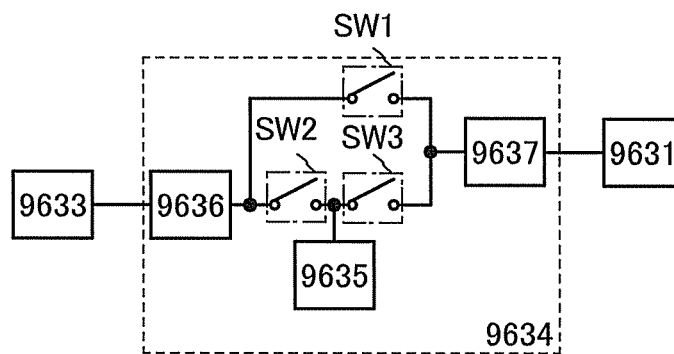


FIG. 12B



PHOTOELECTRIC CONVERSION DEVICE**BACKGROUND OF THE INVENTION****1. Field of the Invention**

The technical field relates to a photoelectric conversion device and a method for manufacturing the photoelectric conversion device.

2. Description of the Related Art

Global warming gets serious and clean energy has attracted attention because a greenhouse effect gas is not generated in producing such energy. Photoelectric conversion devices such as solar cells are typical devices for producing clean energy and are being actively developed and put to practical use throughout the world.

However, current solar cells do not have sufficient performance yet. A tandem solar cell in which a plurality of cells are stacked for improvement in performance is widely known. In addition, a tandem solar cell as disclosed in Patent Document 1 for improvement in power generation efficiency is proposed.

REFERENCE**Patent Document**

[Patent Document 1] Japanese Published Patent Application No. H11-274532

SUMMARY OF THE INVENTION

It is an object of an embodiment of the present invention to provide a photoelectric conversion device whose photoelectric conversion efficiency is improved.

It is an object of another embodiment of the present invention to provide a photoelectric conversion device which outputs high voltage.

It is an object of another embodiment of the present invention to provide a photoelectric conversion device which outputs large current.

It is an object of another embodiment of the present invention to provide a photoelectric conversion device whose output characteristics (current-voltage characteristics) are improved.

According to an embodiment of the present invention, a photoelectric conversion device includes: a first cell including a photoelectric conversion layer, a second cell stacked over the first cell and including a photoelectric conversion layer formed of a material having a wider band gap than that of the first cell, a first electrode and a second electrode provided under a surface of the first cell which is opposite to the second cell, and a third electrode provided over a surface of the second cell which is opposite to the first cell. The first cell and the second cell each include a p-n junction or a p-i-n junction therein, the first cell and the second cell are in contact with each other and a p-n junction is formed in a contact portion therebetween, the first cell is electrically connected to the first electrode and the second electrode to form a back contact structure, and the second cell is electrically connected to the third electrode.

According to another embodiment of the present invention, a photoelectric conversion device includes: a first cell including a photoelectric conversion layer, a second cell stacked over the first cell and including a photoelectric conversion layer formed of a material having a wider band gap than that of the first cell, an insulating layer provided between the first cell and the second cell and including an opening, a first

electrode and a second electrode provided under a surface of the first cell which is opposite to the second cell, and a third electrode provided over a surface of the second cell which is opposite to the first cell. The first cell and the second cell each include a p-n junction or a p-i-n junction therein, the first cell and the second cell are in contact with each other through the opening provided in the insulating layer and a p-n junction is formed in a contact portion therebetween, the first cell is electrically connected to the first electrode and the second electrode to form a back contact structure, and the second cell is electrically connected to the third electrode.

In the above structure, the photoelectric conversion layer included in the first cell can be formed of single crystal silicon or polycrystalline silicon, and the photoelectric conversion layer included in the second cell can be formed of amorphous silicon.

In the above structure, voltage can be obtained between the first electrode and the third electrode and between the first electrode and the second electrode.

In the above structure, current can be obtained between the first electrode and the third electrode and between the first electrode and the second electrode.

The term “photoelectric conversion layer” in this specification includes a semiconductor layer (a semiconductor region) by which a photoelectric effect (an internal photoelectric effect) is achieved and moreover an impurity semiconductor layer (an impurity semiconductor region) which is provided to form an internal electric field or a semiconductor junction. That is, a photoelectric conversion layer in this specification refers to a semiconductor layer having a junction typified by a p-i-n junction or the like.

The term “p-i-n junction” in this specification includes a junction in which a p-type semiconductor layer, an i-type semiconductor layer, and an n-type semiconductor layer are stacked in this order from the light-incidence side and a junction in which an n-type semiconductor layer, an i-type semiconductor layer, and a p-type semiconductor layer are stacked in this order from the light-incidence side.

The ordinal numbers such as “first”, “second”, and “third” in this specification are used for convenience to distinguish elements. Therefore, these ordinal numbers do not limit the number, the arrangement, and the order of steps.

In accordance with an embodiment of the present invention, it is possible to provide a photoelectric conversion device whose photoelectric conversion efficiency is improved. In accordance with another embodiment of the present invention, it is possible to provide a photoelectric conversion device which outputs high voltage. In accordance with another embodiment of the present invention, it is possible to provide a photoelectric conversion device which outputs large current. In accordance with another embodiment of the present invention, it is possible to provide a photoelectric conversion device whose output characteristics (current-voltage characteristics) are improved.

BRIEF DESCRIPTION OF THE DRAWINGS

FIG. 1 is a schematic cross-sectional view illustrating an example of a photoelectric conversion device.

FIGS. 2A to 2C are schematic plan views illustrating an example of a photoelectric conversion device.

FIG. 3 is a view illustrating a conventional example of a photoelectric conversion device.

FIG. 4 is a graph showing examples of characteristics of photoelectric conversion devices.

FIGS. 5A and 5B are diagrams illustrating energy band structures of a photoelectric conversion device.

FIGS. 6A and 6B are diagrams illustrating energy band structures of a photoelectric conversion device.

FIGS. 7A and 7B are diagrams illustrating energy band structures of a photoelectric conversion device.

FIGS. 8A and 8B are diagrams illustrating energy band structures of a photoelectric conversion device of a conventional example.

FIGS. 9A and 9B are diagrams illustrating energy band structures of a photoelectric conversion device of a conventional example.

FIGS. 10A and 10B are diagrams illustrating energy band structures of a photoelectric conversion device of a conventional example.

FIG. 11 is a schematic cross-sectional view illustrating another example of a photoelectric conversion device.

FIGS. 12A and 12B are views illustrating an example of an electronic device.

DETAILED DESCRIPTION OF THE INVENTION

Hereinafter, embodiments will be described in detail with reference to the accompanying drawings. However, since the embodiments described below can be embodied in many different modes, it is easily understood by those skilled in the art that modes and details thereof can be variously changed without departing from the spirit and the scope of the present invention. Therefore, the present invention should not be interpreted as being limited to the following description of the embodiments. In all the drawings for explaining the embodiments, the same portions or portions having similar functions are denoted with the same reference numerals and description of such portions is not repeated. (Embodiment 1)

In this embodiment, a structure of a photoelectric conversion device according to an embodiment of the present invention will be described.

FIG. 1 is an example of a schematic cross-sectional view of a photoelectric conversion device according to this embodiment. FIG. 2A is an example of a schematic plan view of the photoelectric conversion device according to this embodiment. FIG. 1 illustrates a cross section along dashed and dotted line x-y in FIG. 2A.

A photoelectric conversion device 100 includes a first cell 120, a second cell 140 stacked over the first cell 120, a first electrode 101a and a second electrode 101b which are electrically connected to the first cell 120, and a third electrode 107 electrically connected to the second cell 140. The first electrode 101a and the second electrode 101b are provided so as to be connected to the first cell 120 at a surface which is opposite to the second cell 140. The third electrode 107 is provided so as to be connected to the second cell 140 at a surface which is opposite to the first cell 120. The first electrode 101a and the second electrode 101b serve as rear electrodes, and the third electrode 107 serves as a grid electrode.

One surface of the first cell 120 is in contact with the second cell 140, and the other surface thereof is provided with the first electrode 101a and the second electrode 101b. The first electrode 101a and the second electrode 101b are electrically isolated from each other and electrically connected to the first cell 120 separately.

One surface of the second cell 140 is in contact with the first cell 120, and the other surface thereof is provided with the third electrode 107. In this embodiment, the other surface of the second cell 140 is also provided with a transparent conductive film 109. The third electrode 107 is provided over the other surface of the second cell 140 with the transparent

conductive film 109 provided therebetween and electrically connected to the second cell 140.

The first cell 120 and the second cell 140 each include a p-n junction or a p-i-n junction therein. In addition, the first cell 120 and the second cell 140 are in contact with each other, and a p-n junction is formed in a contact portion therebetween.

The first cell 120 and the second cell 140 are formed such that the first cell 120 includes a material whose band gap is narrow (also referred to as a narrow-gap material) and the second cell 140 includes a material whose band gap is wide (also referred to as a wide-gap material), when the band gap of a material used for forming a photoelectric conversion layer in the first cell 120 and the band gap of a material used for forming a photoelectric conversion layer in the second cell 140 are compared with each other. When the second cell 140 provided on the light-receiving side is formed using a material having a wider band gap than that of the first cell 120, photoelectric conversion can be performed efficiently. For example, the first cell 120 is formed using single crystal silicon (whose band gap is about 1.12 eV) or polycrystalline silicon, whereas the second cell 140 is formed using amorphous silicon (whose band gap is about 1.6 eV to 1.8 eV).

Note that light in a short wavelength range (including a visible light range) has higher energy than light in a long wavelength range and is thus easily absorbed. Therefore, when the light penetration depths are compared, light in a short wavelength range has a shallow penetration depth, and light in a long wavelength range has a deep penetration depth. When energy is compared, light in a short wavelength range has high energy, and light in a long wavelength range has low energy; thus, it is preferable that light in a short wavelength range be absorbed in the second cell 140 having a wide band gap and light in a long wavelength range be absorbed in the first cell 120 having a narrow band gap. From the above, it is preferable to form a tandem junction by providing the second cell 140 formed using a wide-gap material on the light-receiving side and providing the first cell 120 formed using a narrow-gap material on the rear surface side. With this structure, part of energy obtained from light absorbed by the photoelectric conversion layer in the photoelectric conversion device, which is greater than or equal to that of the energy band gap of the photoelectric conversion layer in the photoelectric conversion device, can be prevented from being lost as thermal energy; thus, power can be generated efficiently.

The first cell 120 includes a third impurity semiconductor layer 125n and a fourth impurity semiconductor layer 127p. The third impurity semiconductor layer 125n includes a partly provided first impurity semiconductor region 121n⁺ and a partly provided second impurity semiconductor region 123p⁺. In the first cell 120, a photoelectric conversion layer is formed with the third impurity semiconductor layer 125n and the fourth impurity semiconductor layer 127p.

The first impurity semiconductor region 121n⁺ and the second impurity semiconductor region 123p⁺ are isolated from each other. For example, as illustrated in FIG. 2C, the first impurity semiconductor region 121n⁺ and the second impurity semiconductor region 123p⁺ are provided so as to be isolated from each other. The fourth impurity semiconductor layer 127p is stacked over the third impurity semiconductor layer 125n.

One side of the third impurity semiconductor layer 125n is in contact with the fourth impurity semiconductor layer 127p, and the other side thereof is provided with the first impurity semiconductor region 121n⁺ and the second impurity semiconductor region 123p⁺.

One of the first impurity semiconductor region 121n⁺ and the second impurity semiconductor region 123p⁺ is an n-type

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semiconductor region, and the other is a p-type semiconductor region. The n-type semiconductor region (or an n-type semiconductor layer) is a semiconductor region (or a semiconductor layer) containing an impurity element imparting n-type conductivity (e.g., an element belonging to Group 15 of the periodic table, such as phosphorus). The first impurity semiconductor region **121n**⁺ and the second impurity semiconductor region **123p**⁺ can be formed by using single crystal silicon or polycrystalline silicon as a semiconductor layer to which an impurity is added. In addition, amorphous silicon or microcrystalline silicon may be used in addition to single crystal silicon and polycrystalline silicon. Further, carbon or nitrogen may be added to amorphous silicon or microcrystalline silicon. The p-type semiconductor region (or a p-type semiconductor layer) is a semiconductor region (or a semiconductor layer) containing an impurity element imparting p-type conductivity (e.g., an element belonging to Group 13 of the periodic table, such as boron). In this embodiment, an example in which the first impurity semiconductor region **121n**⁺ is an n-type semiconductor region formed using crystalline silicon and the second impurity semiconductor region **123p**⁺ is a p-type semiconductor region formed using crystalline silicon is described.

One of the third impurity semiconductor layer **125n** and the fourth impurity semiconductor layer **127p** is an n-type semiconductor layer, and the other is a p-type semiconductor layer. As described above, for example, the n-type semiconductor layer is a semiconductor layer containing phosphorus or the like and the p-type semiconductor layer is a semiconductor layer containing boron or the like. The third impurity semiconductor layer **125n** and the fourth impurity semiconductor layer **127p** can be formed by using single crystalline silicon or polycrystalline silicon as a semiconductor layer to which an impurity is added. In order to improve transmissivity, in addition to single crystal silicon and polycrystalline silicon, amorphous silicon or microcrystalline silicon can be used as a semiconductor layer to which an impurity is added. Further, carbon or nitrogen may be added to amorphous silicon or microcrystalline silicon. In this embodiment, an example in which the third impurity semiconductor layer **125n** is an n-type semiconductor layer formed using crystalline silicon and the fourth impurity semiconductor layer **127p** is a p-type semiconductor layer formed using crystalline silicon is described.

The first impurity semiconductor region **121n**⁺ is electrically connected to the first electrode **101a**, and the second impurity semiconductor region **123p**⁺ is electrically connected to the second electrode **101b**. For example, an insulating layer **105** provided with openings as illustrated in FIG. 2B is provided on the first impurity semiconductor region **121n**⁺ and the second impurity semiconductor region **123p**⁺, and the first impurity semiconductor region **121n**⁺ and the first electrode **101a** are connected to each other through the opening provided in the insulating layer **105**. The second impurity semiconductor region **123p**⁺ and the second electrode **101b** are connected to each other in a manner similar to the above. Electric connection between the first impurity semiconductor region **121n**⁺ and the first electrode **101a** and electric connection between the second impurity semiconductor region **123p**⁺ and the second electrode **101b** can be easily separated from each other with the insulating layer **105**.

For example, the first electrode **101a** and the second electrode **101b** are formed using aluminum, and the insulating layer **105** is formed using silicon oxide. The first electrode **101a** and the second electrode **101b** are arranged so as to cover the entire rear surface as much as possible, unless they are in electric contact with each other. The insulating layer

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105 is formed to a thickness of greater than or equal to 10 nm and less than or equal to 160 nm, preferably greater than or equal to 60 nm and less than or equal to 140 nm. In such a manner, as well as electric isolation between the first impurity semiconductor region **121n**⁺ and the second impurity semiconductor region **123p**⁺, light reflectivity of the first electrode **101a** and the second electrode **101b** provided on the rear surface side can be increased, whereby the amount of light absorption in the photoelectric conversion layer can be increased and photoelectric current can be increased.

The first electrode **101a** and the second electrode **101b** are positioned opposite to the light-receiving side of the photoelectric conversion device **100**. The structure with the first electrode **101a** and the second electrode **101b** as illustrated in FIG. 1 and FIG. 2A is referred to as a so-called back contact structure or rear electrode type.

The second cell **140** includes a fifth impurity semiconductor layer **141n**, a sixth semiconductor layer **143i**, and a seventh impurity semiconductor layer **145p**. In the second cell **140**, a photoelectric conversion layer is formed with the fifth impurity semiconductor layer **141n**, the sixth semiconductor layer **143i**, and the seventh impurity semiconductor layer **145p**. The sixth semiconductor layer **143i** is stacked over the fifth impurity semiconductor layer **141n**, and the seventh impurity semiconductor layer **145p** is stacked over the sixth semiconductor layer **143i**.

One surface of the fifth impurity semiconductor layer **141n** is in contact with the fourth impurity semiconductor layer **127p** of the first cell **120**, and the other surface thereof is in contact with the sixth semiconductor layer **143i**. In this embodiment, the fifth impurity semiconductor layer **141n** and the fourth impurity semiconductor layer **127p** form a p-n junction. That is, a p-n junction is formed at a contact surface between the second cell **140** and the first cell **120**.

In this embodiment, an example in which the fourth impurity semiconductor layer **127p** is a p-type semiconductor layer is described. Therefore, the fifth impurity semiconductor layer **141n** is an n-type semiconductor layer. It is needless to say that when the fourth impurity semiconductor layer **127p** is an n-type semiconductor layer, the fifth impurity semiconductor layer **141n** is a p-type semiconductor layer.

The sixth semiconductor layer **143i** is an intrinsic or substantially intrinsic semiconductor layer. Specifically, the concentration of an impurity element which imparts n-type conductivity or p-type conductivity and is contained in the sixth semiconductor layer **143i** is less than or equal to $1 \times 10^{18}/\text{cm}^3$, and photoconductivity of the sixth semiconductor layer **143i** is greater than or equal to 100 times of dark conductivity thereof. In the case where the sixth semiconductor layer **143i** is an amorphous semiconductor layer, the semiconductor layer exhibits low n-type conductivity in some cases when no impurity element for controlling valence electrons is added thereto intentionally. Therefore, an impurity element imparting p-type conductivity may be added during or after formation of the amorphous semiconductor layer. In such a case, the concentration of a p-type impurity element contained in the amorphous semiconductor layer is about $1 \times 10^{14}/\text{cm}^3$ to $6 \times 10^{16}/\text{cm}^3$.

One surface of the seventh impurity semiconductor layer **145p** is in contact with the sixth semiconductor layer **143i**, and the other surface thereof is provided with the third electrode **107**. In this embodiment, the other surface of the seventh impurity semiconductor layer **145p** is also provided with the transparent conductive film **109**, and the third electrode **107** is provided over the seventh impurity semiconductor layer **145p** with the transparent conductive film **109** provided therebetween.

The seventh impurity semiconductor layer **145p** is an impurity semiconductor layer having a conductivity type opposite to that of the fifth impurity semiconductor layer **141n**. Since an example in which the fifth impurity semiconductor layer **141n** is an n-type semiconductor layer is described in this embodiment, the seventh impurity semiconductor layer **145p** is a p-type semiconductor layer.

The third electrode **107** is positioned on the light-receiving side of the photoelectric conversion device **100**. It is preferable that, on the light-receiving side, light (the sunlight) can be received in an area that is as large as possible. Therefore, on the light-receiving side, the third electrode **107** is provided partly, and the transparent conductive film **109** is provided between the third electrode **107** and the second cell **140** (the seventh impurity semiconductor layer **145p**). With the transparent conductive film **109**, light reception is not hindered, and power can be generated efficiently. In addition, with the third electrode **107**, series resistance can be reduced.

In order to reduce reflectivity on the light-receiving side, an anti-reflection film may be provided with the use of a material having a refractive index that is between refractive indices of the air and the transparent conductive film **109** over a region of the transparent conductive film **109**, which is not provided with the third electrode **107**. The anti-reflection film may have a single-layer structure or a layered structure. Alternatively, a texture structure in which the surface of the transparent conductive film **109** is made uneven may be used. The texture structure can reduce reflectivity on the light-receiving side. Accordingly, optical loss due to reflection at the light-receiving surface is reduced, and the amount of light absorption in the photoelectric conversion layer is increased, whereby photoelectric current can be increased and photoelectric conversion efficiency can be improved.

In the photoelectric conversion device **100** illustrated in FIG. 1 and FIGS. 2A to 2C, voltage and current can be obtained between the first electrode **101a** and the second electrode **101b** as well as between the first electrode **101a** and the third electrode **107**. All of voltage and current obtained between the first electrode **101a** and the third electrode **107** and voltage and current obtained between the first electrode **101a** and the second electrode **101b** can be used. Therefore, the total output of the photoelectric conversion device **100** can be high, and output characteristics (current-voltage characteristics) can be improved, so that a photoelectric conversion device with high photoelectric conversion efficiency can be provided.

This embodiment can be combined with any of other embodiments as appropriate. (Embodiment 2)

In this embodiment, characteristics of the photoelectric conversion device **100** described in Embodiment 1 will be described by being compared with those of a solar cell with a three-terminal structure disclosed in Patent Document 1 as appropriate.

FIG. 3 illustrates a cross section of a solar cell **10** corresponding to FIG. 1 of Patent Document 1. The solar cell **10** has a structure in which an upper cell **12** having a wide band gap and a lower cell **14** having a narrow band gap are stacked. The upper cell **12** includes an n⁺-layer (**46n**), a p-layer (**44p**), and a p⁺-layer (**42p⁺**) which are stacked. An upper electrode **18** is provided over the n⁺-layer (**46n**) of the upper cell **12** with an insulating film **24** provided therebetween.

In the lower cell **14**, an n⁺-layer (**32n⁺**) and a p⁺-layer (**34p⁺**) are alternately provided on a rear surface side of a p-layer (**36p**). A negative electrode **26** and a positive electrode **28** are connected to the n⁺-layer (**32n⁺**) and the p⁺-layer (**34p⁺**), respectively.

The solar cell **10** illustrated in FIG. 3 has a three-terminal structure in which the upper electrode **18**, the negative electrode **26**, and the positive electrode **28** are connected to the n⁺-layer (**46n**) of the upper cell **12**, the n⁺-layer (**32n⁺**) of the lower cell **14**, and the p⁺-layer (**34p⁺**) of the lower cell **14**, respectively. The p-layer (**36p**) of the lower cell **14** and the p⁺-layer (**42p⁺**) of the upper cell **12** are in contact with each other.

The photoelectric conversion device **100** illustrated in FIG. 1 of Embodiment 1 includes the n-layer and the p-layer which are sequentially stacked in the first cell **120**, and the n-layer, the i-layer, and the p-layer which are sequentially stacked in the second cell **140**. On the other hand, the solar cell **10** illustrated in FIG. 3 includes the p-layer in the lower cell **14** corresponding to the first cell, and the p-layer, and the n-layer which are sequentially stacked in the upper cell **12** corresponding to the second cell.

In the photoelectric conversion device **100** illustrated in FIG. 1, a diode junction of a vertical direction is formed in each of the first cell **120** and the second cell **140**. On the other hand, in the solar cell **10** illustrated in FIG. 3, the n-layer and the p-layer are formed in the upper cell **12** but only the p-layer is formed in the lower cell **14**; this structure is different from that of the photoelectric conversion device illustrated in FIG. 1. In addition, although a p-n junction is formed at a junction between the first cell **120** and the second cell **140** in the photoelectric conversion device **100** illustrated in FIG. 1, the p⁺-layer and the p-layer are in contact with each other at a junction between the upper cell **12** and the lower cell **14** in the solar cell **10** illustrated in FIG. 3; this structure is different from that of the photoelectric conversion device **100** illustrated in FIG. 1.

FIG. 4 shows I-V characteristics assumed for the photoelectric conversion device **100** illustrated in FIG. 1 and I-V characteristics assumed for the solar cell **10** illustrated in FIG. 3. Characteristics (I) in FIG. 4 are characteristics in (I) (between the third electrode **107** and the first electrode **101a**) in FIG. 1, and characteristics (III) in FIG. 4 are characteristics in (III) (between the first electrode **101a** and the second electrode **101b**) in FIG. 1. Characteristics (i) in FIG. 4 are characteristics in (i) (between the positive electrode **28** and the upper electrode **18**) in FIG. 3, and characteristics (iii) in FIG. 4 are characteristics in (iii) (between the positive electrode **28** and the negative electrode **26**) in FIG. 3.

The photoelectric conversion device **100** illustrated in FIG. 1 has a tandem junction including plural diode junctions in which the first cell **120** having a diode junction and the second cell **140** having a diode junction are stacked. On the other hand, since the lower cell **14** has only one polarity (the p-layer), the solar cell **10** illustrated in FIG. 3 has a tandem junction in which the upper cell **12** and the lower cell **14** include one diode junction as a whole. Therefore, voltage obtained in the solar cell **10** in FIG. 3 is lower than that in the case of the tandem junction including plural diode junctions. Specifically, as is clear from (I) and (i) in FIG. 4, there is a difference in output voltage. High voltage can be obtained in (I) of the photoelectric conversion device **100**, as compared with the solar cell **10**.

FIGS. 5A and 5B illustrate energy band structures of (I) in the photoelectric conversion device **100** illustrated in FIG. 1. FIG. 5A illustrates an energy band structure in an equilibrium state, and FIG. 5B illustrates an energy band structure at the time of light irradiation. Here, an example in which light enters from the second cell **140** side is illustrated. In addition, an example in which the first cell **120** in FIG. 1 is formed

using single crystal silicon or polycrystalline silicon and the second cell **140** in FIG. **1** is formed using amorphous silicon is described.

Voltage **V** in FIG. **5B** which is obtained in (I) of the photoelectric conversion device **100** equals to the sum of voltage that is obtained in the case where a photoelectric conversion device of a single junction is formed in the first cell **120** and voltage that is obtained in the case where a photoelectric conversion device of a single junction is formed in the second cell **140** (see **V(101a~107)** in FIG. **5B**).

As a reference, FIGS. **8A** and **8B** illustrate energy band structures of (i) in the solar cell **10** illustrated in FIG. **3**. FIG. **8A** illustrates an energy band structure in an equilibrium state, and FIG. **8B** illustrates an energy band structure at the time of light irradiation.

Voltage **V** in FIG. **8B** which is obtained in (i) of the solar cell **10** is equal to voltage that is obtained in the case where a photoelectric conversion device of a single junction is formed in the upper cell **12** (see **V(28~18)** in FIG. **8B**).

As shown in FIGS. **5A** and **5B**, in (I) of the photoelectric conversion device **100** illustrated in FIG. **1**, voltage equal to the sum of voltage that is obtained in the case where a photoelectric conversion device of a single junction is formed in the first cell **120** and voltage that is obtained in the case where a photoelectric conversion device of a single junction is formed in the second cell **140** can be obtained. On the other hand, as shown in FIGS. **8A** and **8B**, voltage that is obtained in (i) of the solar cell **10** illustrated in FIG. **3** is substantially equal to only a voltage that is obtained in the case where a photoelectric conversion device of a single junction is formed in the upper cell **12** corresponding to the second cell.

As described above, higher voltage can be obtained in the photoelectric conversion device **100** illustrated in FIG. **1** than in the solar cell **10** illustrated in FIG. **3**. In addition, since high voltage can be obtained in the photoelectric conversion device **100** illustrated in FIG. **1**, photoelectric conversion efficiency thereof can be improved.

FIGS. **6A** and **6B** and FIGS. **7A** and **7B** illustrate energy band structures of (II) (between the third electrode **107** and the second electrode **101b**) and energy band structures of (III) in the photoelectric conversion device **100** illustrated in FIG. **1**, respectively. FIG. **6A** and FIG. **7A** illustrate energy band structures in an equilibrium state, and FIG. **6B** and FIG. **7B** illustrate energy band structures at the time of light irradiation. As a reference, FIGS. **9A** and **9B** and FIGS. **10A** and **10B** illustrate energy band structures of (ii) (between the negative electrode **26** and the upper electrode **18**) and energy band structures of (iii) in the solar cell **10** illustrated in FIG. **3**, respectively. FIG. **9A** and FIG. **10A** illustrate energy band structures in an equilibrium state, and FIG. **9B** and FIG. **10B** illustrate energy band structures at the time of light irradiation.

Voltage **V** obtained in (III) of the photoelectric conversion device **100** is equal to voltage that is obtained in the case where a photoelectric conversion device of a single junction is formed in the first cell **120** (see **V(101a~101b)** in FIG. **7B**).

Voltage **V** obtained in (iii) of the solar cell **10** is equal to voltage that is obtained in the case where a photoelectric conversion device of a single junction is formed in the lower cell **14** (see **V(28~26)** in FIG. **10B**).

According to FIGS. **7A** and **7B** and FIGS. **10A** and **10B**, voltage obtained between the rear electrodes, that is, voltage obtained between the first electrode **101a** and the second electrode **101b** in the photoelectric conversion device **100** of FIG. **1** and voltage obtained between the positive electrode **28** and the negative electrode **26** in the solar cell **10** of FIG. **3**, are each substantially equal to voltage that is obtained in the case

where a photoelectric conversion device of a single junction is formed in a cell provided on the rear surface side. However, in the photoelectric conversion device **100** illustrated in FIG. **1**, high voltage can be obtained in (I) as described above. Therefore, in the entire photoelectric conversion device **100** illustrated in FIG. **1**, higher voltage can be obtained than in the solar cell **10** illustrated in FIG. **3**, so that the total output of the photoelectric conversion device **100** can be high.

Next, operation mechanism at the time of light irradiation in the photoelectric conversion device **100** illustrated in FIG. **1** will be described.

In the photoelectric conversion device **100**, the second cell **140** including a diode junction formed of a wide-gap material and the first cell **120** including a diode junction formed of a narrow-gap material are arranged in this order from the light-receiving side. The second cell **140** and the first cell **120** are connected in series. In order to absorb light efficiently, the cell on the light-receiving side of the photoelectric conversion device is preferably formed of a wide-gap material, and the cell on the rear surface side is preferably formed of a narrow-gap material.

Here, light in a short wavelength range (including a visible light range) is more easily absorbed than light in a long wavelength range. Therefore, when the light penetration depths are compared, light in a short wavelength range has a shallow penetration depth, and light in a long wavelength range has a deep penetration depth. When energy is compared, light in a short wavelength range has high energy, and light in a long wavelength range has low energy; thus, it is preferable that light in a short wavelength range be absorbed in the second cell **140** having a wide band gap and light in a long wavelength range be absorbed in the first cell **120** having a narrow band gap. From the above, it is preferable to form a tandem junction by providing the second cell **140** formed using a wide-gap material on the light-receiving side and providing the first cell **120** formed using a narrow-gap material on the rear surface side. With this structure, part of energy obtained from light absorbed by the photoelectric conversion layer in the photoelectric conversion device, which is greater than or equal to that of the energy band gap of the photoelectric conversion layer in the photoelectric conversion device, can be prevented from being lost as thermal energy; thus, power can be generated efficiently.

Current **I(101a~107)** obtained between the third electrode **107** and the first electrode **101a** is substantially equal to current obtained in the first cell **120** or current obtained in the second cell **140**, whichever is small. This is because a p-n junction is formed at a junction between the first cell **120** and the second cell **140**, carriers from the first cell **120** and the second cell **140** are recombined at the junction, and current flowing through the first cell **120** and current flowing through the second cell **140** which are connected in series are substantially equal to each other.

In the case where the second cell **140** formed of a wide-gap material and the first cell **120** formed of a narrow-gap material are arranged in this order from the light-receiving side, light in a narrower wavelength range is absorbed and smaller current is obtained in the second cell **140** than in the first cell **120**. Accordingly, current **I** obtained between the third electrode **107** and the first electrode **101a** is substantially equal to current obtained in the second cell **140**.

On the other hand, in the first cell **120** formed of a narrow-gap material, light in a wider wavelength range is absorbed and larger current is obtained than in the second cell **140**. In the first cell **120**, current equal to that in the second cell **140** flows owing to carrier recombination at a junction between the first cell **120** and the second cell **140** and the current is

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obtained between the third electrode **107** and the first electrode **101a** (through a path of (I)). Current corresponding to carriers that remain in the first cell **120** without being recombined at the junction between the first cell **120** and the second cell **140** can be obtained between the first electrode **101a** and the second electrode **101b** (through a path of (III)). With the above structure, particularly, with a three-terminal structure including the path of (III), all the current can be obtained without remaining. The amount of current that can be obtained can be increased in the entire photoelectric conversion device **100**, so that photoelectric conversion efficiency can be improved.

Operation mechanism of the photoelectric conversion device **100** will be described with reference FIGS. **5A** and **5B**, FIGS. **6A** and **6B**, and FIGS. **7A** and **7B**. Note that FIGS. **5A** and **5B**, FIGS. **6A** and **6B**, and FIGS. **7A** and **7B** illustrate the energy band structures of (I), the energy band structures of (II), and the energy band structures of (III) in the photoelectric conversion device **100** illustrated in FIG. **1**, respectively.

At the time of light irradiation in the photoelectric conversion device **100** which is illustrated in FIG. **5B**, holes generated by light absorption in the second cell **140** can be taken out as current from the third electrode **107**. Electrons generated by light absorption in the second cell **140** are recombined with part of holes generated in the first cell **120** at the junction between the cells, so that current flows. Electrons generated by light absorption in the first cell **120** can be taken out as current from the first electrode **101a**. The other part of holes generated by light absorption in the first cell **120**, which are not recombined at the junction between the cells, can be taken out as current from the second electrode **101b** through the path of (III) in FIG. **1**.

The energy band structure illustrated in FIG. **5B** shows that current which can be obtained between the third electrode **107** and the first electrode **101a** is substantially equal to current generated by light absorption in the second cell **140**.

At the time of light irradiation illustrated in FIG. **6B**, holes generated by light absorption in the second cell **140** can be taken out as current from the third electrode **107**. Electrons generated by light absorption in the second cell **140** are recombined with part of holes generated by light absorption in the first cell **120** at the junction between the cells, so that current flows. Electrons generated by light absorption in the second cell **120** can be taken out as current from the first electrode **101a** through the path of (III). The other part of holes generated by light absorption in the second cell **120**, which are not recombined at the junction between the cells, can be taken out as current from the second electrode **101b** through the path of (III).

At the time of light irradiation illustrated in FIG. **7B**, holes generated by light absorption in the first cell **120** can be taken out as current from the second electrode **101b**, and electrons generated by light absorption in the first cell **120** can be taken out as current from the first electrode **101a**.

From the energy band structures illustrated in FIG. **5B**, FIG. **6B**, and FIG. **7B**, it is found that current corresponding to carriers which are not recombined at the junction between the first cell **120** and the second cell **140** and remain in the first cell **120** can be obtained between the first electrode **101a** and the second electrode **101b**.

As described above, by employing the structure of the photoelectric conversion device **100** illustrated in FIG. **1** and taking out all the current, the amount of current that can be obtained in the entire photoelectric conversion device **100** can be increased, so that photoelectric conversion efficiency can be improved.

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For comparison, a difference from operation mechanism of the solar cell **10** illustrated in FIG. **3** will be described. FIGS. **8A** and **8B**, FIGS. **9A** and **9B**, and FIGS. **10A** and **10B** illustrate the energy band structures of (i), the energy band structures of (ii), and the energy band structures of (iii) in the solar cell **10** illustrated in FIG. **3** respectively.

The upper cell **12** of the solar cell **10** corresponds to the second cell **140** of the photoelectric conversion device **100**. In a similar manner, the lower cell **14**, the upper electrode **18**, the positive electrode **28**, and the negative electrode **26** correspond to the first cell **120**, the third electrode **107**, the first electrode **101a**, and the second electrode **101b**, respectively.

At the time of light irradiation in the solar cell **10** which is illustrated in FIG. **8B**, holes generated by light absorption in the upper cell **12** can be taken out as current from the positive electrode **28**. Electrons generated by light absorption in the upper cell **12** can be taken out as current from the upper electrode **18**. Holes generated by light absorption in the lower cell **14** can be taken out as current from the positive electrode **28**. Electrons generated by light absorption in the lower cell **14** can be taken out as current from the negative electrode **26** through a path of (iii).

From the energy band structure illustrated in FIG. **8B**, it is found that since the lower cell **14** has only one polarity (the p-layer) and a p-n junction is not formed at the junction between the lower cell **14** and the upper cell **12**, current due to holes can be obtained between the positive electrode **28** and the upper electrode **18** in (i) of the solar cell **10** illustrated in FIG. **3**. Fermi levels and potentials of the p-layer in the lower cell **14** and the p⁺-layer (**42p⁺**) in the upper cell **12** are substantially equal to each other, and an energy barrier between the p-layer in the lower cell **14** and the p⁺-layer (**42p⁺**) in the upper cell **12** is small, so that holes move without being recombined at the junction between the lower cell **14** and the upper cell **12**.

At the time of light irradiation which is illustrated in FIG. **9B**, holes generated by light absorption in the upper cell **12** can be taken out as current from the positive electrode **28** through the path of (i). Electrons generated by light absorption in the upper cell **12** can be taken out as current from the upper electrode **18**. Holes generated by light absorption in the lower cell **14** can be taken out as current from the positive electrode **28**. Electrons generated by light absorption in the lower cell **14** can be taken out as current from the negative electrode **26**.

At the time of light irradiation illustrated in FIG. **10B**, holes generated by light absorption in the lower cell **14** can be taken out as current from the positive electrode **28**, and electrons generated by light absorption in the lower cell **14** can be taken out as current from the negative electrode **26**.

Comparison of FIGS. **5A** and **5B**, FIGS. **6A** and **6B**, and FIGS. **7A** and **7B** with FIGS. **8A** and **8B**, FIGS. **9A** and **9B**, and FIGS. **10A** and **10B** shows a difference in operation mechanism between the photoelectric conversion device **100** illustrated in FIG. **1** and the solar cell **10** illustrated in FIG. **3**.

The photoelectric conversion device **100** in FIG. **1** can have the characteristics denoted by (I) and (III) in FIG. **4**, with the energy band structures in FIGS. **5A** and **5B**, FIGS. **6A** and **6B**, and FIGS. **7A** and **7B**. The photoelectric conversion device **100** outputs voltage and current obtained between the third electrode **107** and the first electrode **101a** and between the first electrode **101a** and the second electrode **101b**, which can be used as power. In the photoelectric conversion device **100** illustrated in FIG. **1**, a diode junction of a p-n junction is formed at the junction between the cells, and photoexcited carriers are recombined and current flows in the same direction as a forward direction, so that at the junction, photoelec-

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tromotive force is not generated and Fermi levels and potentials of the cells are substantially equal to each other. Therefore, photoelectromotive force generated in the first cell **120** and the second cell **140** can be independently maintained. Electrons and holes recombined at the p-n junction between the first cell **120** and the second cell **140** contribute to voltage obtained between the third electrode **107** and the first electrode **101a**, and the voltage can be utilized. Consequently, photoelectric conversion efficiency can be improved.

This embodiment can be combined with the structure described in any of other embodiments as appropriate. (Embodiment 3)

In this embodiment, a structure which is different from that of the photoelectric conversion device **100** of FIG. **1** described in the above embodiment will be described. Specifically, an example of an emitter structure in which impurity semiconductor regions with varied impurity concentrations are provided on a surface side of a first cell **120**, which faces a second cell **140**, will be described. Note that components which are the same as those in FIG. **1** are denoted by the same reference numerals, and detailed description of such components is omitted.

A photoelectric conversion device **200** illustrated in FIG. **11** is a tandem photoelectric conversion device in which the first cell **120** and the second cell **140** are sequentially stacked as in the photoelectric conversion device **100** illustrated in FIG. **1**.

On the surface side of the first cell **120** which faces the second cell **140**, not a semiconductor layer having a uniform impurity concentration but an impurity semiconductor layer including semiconductor regions having varied impurity concentrations is provided. For example, as illustrated in FIG. **11**, an emitter structure provided with a fourth impurity semiconductor layer **228p** is used. The fourth impurity semiconductor layer **228p** includes a fourth high-concentration impurity semiconductor region **226p⁺** and a fourth low-concentration impurity semiconductor region **227p⁻**. The fourth high-concentration impurity semiconductor region **226p⁺** and the fourth low-concentration impurity semiconductor region **227p⁻** contain an impurity element at different concentrations, for example. Here, the fourth high-concentration impurity semiconductor region **226p⁺** contains an impurity element at a higher concentration than in the fourth low-concentration impurity semiconductor region **227p⁻**. In this embodiment, an example in which the fourth high-concentration impurity semiconductor region **226p⁺** and the fourth low-concentration impurity semiconductor region **227p⁻** are p-type semiconductor regions is described.

An insulating layer **230** is provided between the first cell **120** and the second cell **140**. The insulating layer **230** is provided with an opening.

The first cell **120** and the second cell **140** are in contact with each other through the opening provided in the insulating layer **230**, and a p-n junction is formed in a contact portion therebetween. Specifically, the opening is provided in the insulating layer **230** such that the fourth high-concentration impurity semiconductor region **226p⁺** included in the first cell **120** is exposed. A fifth impurity semiconductor layer **141n** included in the second cell **140** is provided so as to fill the opening provided in the insulating layer **230**. With such a structure, the fourth high-concentration impurity semiconductor region **226p⁺** and the fifth impurity semiconductor layer **141n** are in contact with each other. In order to form a p-n junction in the contact portion, one of the fourth high-concentration impurity semiconductor region **226p⁺** and the

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fifth impurity semiconductor layer **141n** is formed of a p-type semiconductor, and the other is formed of an n-type semiconductor.

As for basic operation mechanism of the photoelectric conversion device **200** illustrated in FIG. **11**, the description of the energy band structures with reference to FIGS. **5A** and **5B**, FIGS. **6A** and **6B**, and FIGS. **7A** and **7B** is referred to.

In the fourth impurity semiconductor layer **228p**, the fourth high-concentration impurity semiconductor region **226p⁺** is provided only in a region which is joined to the fifth impurity semiconductor layer **141n** of the second cell **140**, and the fourth low-concentration impurity semiconductor region **227p⁻** is formed in the other region, whereby loss of recombination of photoexcited carriers can be reduced in the fourth impurity semiconductor layer **228p**. In addition, by providing the insulating layer **230** between the second cell **140** and the first cell **120**, reflectivity of the fifth impurity semiconductor layer **141n** can be increased, whereby photoelectric current can be increased because the amount of light absorption is increased in the second cell **140**, and the second cell **140** can be thinned owing to light confinement.

With the use of an emitter structure, photoelectric conversion efficiency can be improved. Also when the photoelectric conversion device according to this embodiment is a tandem photoelectric conversion device provided with an emitter structure, high voltage and large current can be obtained, whereby photoelectric conversion efficiency can be improved.

This embodiment can be combined with the structure described in any of other embodiments as appropriate. (Embodiment 4)

The photoelectric conversion device described in any of the above embodiments can be applied to a variety of electronic devices. A plurality of the photoelectric conversion devices described in any of the above embodiments can be connected to be integrated for application. In this embodiment, an example of using the photoelectric conversion device as a power source of an electronic book reader will be described.

FIG. **12A** is a schematic view of an electronic book reader (also referred to as an e-book reader). An electronic book reader **9000** includes housings **9630**, a display area **9631**, operation keys **9632**, a photoelectric conversion device **9633**, and a charge and discharge control circuit **9634**. The electronic book reader **9000** illustrated in FIG. **12A** has a function of displaying various kinds of data (e.g., a still image, a moving image, and a text image) on the display area, a function of displaying a calendar, a date, the time, or the like on the display area, a function of operating or editing the data displayed on the display area, a function of controlling processing by various kinds of software (programs), and the like. In FIG. **12A**, a structure including a battery **9635**, a DCDC converter **9636**, and a DCDC converter **9637** is illustrated as an example of the charge and discharge control circuit **9634**. By employing the photoelectric conversion device described in any of the above embodiments for the photoelectric conversion device **9633**, power can be generated efficiently.

Note that the photoelectric conversion device **9633** can be provided in not only the illustrated region but also a space (a surface or a rear surface) of the housing **9630** as appropriate. When a lithium ion battery is used as the battery **9635**, there is an advantage of downsizing or the like.

The structure and the operation of the charge and discharge control circuit **9634** illustrated in FIG. **12A** will be described with reference to a block diagram in FIG. **12B**. FIG. **12B** illustrates the photoelectric conversion device **9633**, the charge and discharge control circuit **9634**, and the display area **9631**. The battery **9635**, the DCDC converter **9636**, the

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DCDC converter **9637**, and switches SW1 to SW3 are included in the charge and discharge control circuit **9634**.

An example of the operation in the case where power is generated by the photoelectric conversion device **9633** using external light will be described. The voltage of power generated by the photoelectric conversion device is raised or lowered by the DCDC converter **9636** to a suitable voltage for charging the battery **9635**. Then, when performing a display in the display area **9631**, the switch SW1 is turned on, the voltage of the power is raised or lowered in the DCDC converter **9637** to a voltage that is needed in the display area **9631**, and power is supplied to the display area **9631**. When display is not performed in the display area **9631**, the switch SW1 may be turned off and the switch SW2 may be turned on, whereby the battery **9635** can be charged.

In addition, the operation in the case where power is not generated by the photoelectric conversion device **9633** owing to lack of external light will be described. By turning on the switch SW3, the voltage of power that is stored in the battery **9635** is raised or lowered by the DCDC converter **9637** to a voltage that is needed in the display area **9631**, and then supplied to the display area **9631**.

Note that in this embodiment, although two DCDC converters are provided between the photoelectric conversion device and the display area, the DCDC converters therebetween may be omitted in a structure that allows directly supplying power to the display area from the photoelectric conversion device, directly charging the battery from the photoelectric conversion device, or directly supplying power to the display area from the battery.

Note that although an example of using only the photoelectric conversion device **9633** is described as an example of a power generation means, the battery **9635** may be charged by a combination of the photoelectric conversion device **9633** and another photoelectric conversion device with a structure different from that of the photoelectric conversion device **9633**. Furthermore, the combination may be a combination of the photoelectric conversion device **9633** and another power generation means.

This embodiment can be combined with the structure described in any of other embodiments as appropriate.

This application is based on Japanese Patent Application serial no. 2010-138889 filed with Japan Patent Office on Jun. 18, 2010, the entire contents of which are hereby incorporated by reference.

What is claimed is:

1. A photoelectric conversion device comprising:

a first cell including a photoelectric conversion layer;

a second cell stacked over the first cell and including a photoelectric conversion layer formed of a material having a wider band gap than that of the first cell;

a first electrode and a second electrode provided under a surface of the first cell which is opposite to the second cell; and

a third electrode provided over a surface of the second cell which is opposite to the first cell,

wherein the first cell and the second cell each include a p-n junction or a p-i-n junction therein,

wherein the first cell and the second cell are in contact with each other and a p-n junction is formed in a contact portion therebetween,

wherein the first cell is electrically connected to the first electrode and the second electrode to form a back contact structure,

wherein the second cell is electrically connected to the third electrode,

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wherein first voltage and first current are obtained between the first electrode and the third electrode, and wherein second voltage and second current are obtained between the first electrode and the second electrode.

2. The photoelectric conversion device according to claim 1, wherein the third electrode is electrically connected to the second cell via a transparent conductive film.

3. A photoelectric conversion device comprising:

a first cell including a photoelectric conversion layer;

a second cell stacked over the first cell and including a photoelectric conversion layer formed of a material having a wider band gap than that of the first cell;

an insulating layer provided between the first cell and the second cell and including an opening;

a first electrode and a second electrode provided under a surface of the first cell which is opposite to the second cell; and

a third electrode provided over a surface of the second cell which is opposite to the first cell,

wherein the first cell and the second cell each include a p-n junction or a p-i-n junction therein,

wherein the first cell and the second cell are in contact with each other through the opening provided in the insulating layer and a p-n junction is formed in a contact portion therebetween,

wherein the first cell is electrically connected to the first electrode and the second electrode to form a back contact structure,

wherein the second cell is electrically connected to the third electrode,

wherein first voltage and first current are obtained between the first electrode and the third electrode, and

wherein second voltage and second current are obtained between the first electrode and the second electrode.

4. The photoelectric conversion device according to claim 3, wherein the third electrode is electrically connected to the second cell via a transparent conductive film.

5. A photoelectric conversion device comprising:

a first cell including a photoelectric conversion layer;

a second cell stacked over the first cell and including a photoelectric conversion layer formed of a material having a wider band gap than that of the first cell;

a first electrode and a second electrode provided under a surface of the first cell which is opposite to the second cell; and

a third electrode provided over a surface of the second cell which is opposite to the first cell,

wherein the first cell and the second cell each include a p-n junction or a p-i-n junction therein,

wherein the first cell and the second cell are in contact with each other and a p-n junction is formed in a contact portion therebetween,

wherein the first cell is electrically connected to the first electrode and the second electrode to form a back contact structure,

wherein the second cell is electrically connected to the third electrode,

wherein the photoelectric conversion layer included in the first cell comprises single crystal silicon or polycrystalline silicon,

wherein the photoelectric conversion layer included in the second cell comprises amorphous silicon,

wherein first voltage and first current are obtained between the first electrode and the third electrode, and

wherein second voltage and second current are obtained between the first electrode and the second electrode.

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6. The photoelectric conversion device according to claim 5, wherein the third electrode is electrically connected to the second cell via a transparent conductive film.

7. A photoelectric conversion device comprising:

a first cell including a photoelectric conversion layer;

a second cell stacked over the first cell and including a photoelectric conversion layer formed of a material having a wider band gap than that of the first cell;

an insulating layer provided between the first cell and the second cell and including an opening;

a first electrode and a second electrode provided under a surface of the first cell which is opposite to the second cell; and

a third electrode provided over a surface of the second cell which is opposite to the first cell,

wherein the first cell and the second cell each include a p-n junction or a p-i-n junction therein,

wherein the first cell and the second cell are in contact with each other through the opening provided in the insulating layer and a p-n junction is formed in a contact portion therebetween,

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wherein the first cell is electrically connected to the first electrode and the second electrode to form a back contact structure,

wherein the second cell is electrically connected to the third electrode,

wherein the photoelectric conversion layer included in the first cell comprises single crystal silicon or polycrystalline silicon,

wherein the photoelectric conversion layer included in the second cell comprises amorphous silicon,

wherein first voltage and first current are obtained between the first electrode and the third electrode, and

wherein second voltage and second current are obtained between the first electrode and the second electrode.

8. The photoelectric conversion device according to claim 7, wherein the third electrode is electrically connected to the second cell via a transparent conductive film.

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